

Нагорнов Юрий Сергеевич

List of Pub

- [1] Nagornov Yu., Katz A., “Parametrically Temperature-Dependent Potential for Molecular Dynamics Simulation of Uranium Dioxide Properties”, *International Journal of Computational and Theoretical Chemistry*, **1**:3 (2013), 18–26.
- [2] Nagornov Yu.S., Katz A.V., “Calculation of phase transitions of uranium dioxide using structure factor in molecular dynamics”, *International Journal of Materials Science and Applications*, **2**:6 (2013), 228–232.
- [3] Kostishko B.M., Zolotov A.V., Nagornov Yu.S., “Simulation of degradation of the profile of nanoporous silicon in the course of annealing in an inhomogeneous temperature field”, *Semiconductors*, **43**:3 (2009), 355–358 [crossref](#) [ISI Web of Knowledge](#).
- [4] Nagornov Yu.S., Kostishko B.M., Mikov S.N. et al, “Formation of silicon carbide nanocrystals by high-temperature carbonization of porous silicon”, *Technical Physics*, **52**:8 (2007), 1093–1097 [crossref](#) [ISI Web of Knowledge](#).
- [5] Kostishko B.M., Nagornov Yu.S., Appolonov S.V., “The modification of the properties of n-type conductivity porous silicon by argon ion irradiation”, *Vacuum*, **73**:1 (2004), 105–108 [crossref](#) [ISI Web of Knowledge](#).
- [6] Kostishko B.M., Nagornov Yu.S., Salomatin S.Ya., Atazhanov Sh.R., “The interface mechanism of photoluminescence in carbonized porous silicon”, *Technical Physics Letters*, **30**:2 (2004), 88–90 [crossref](#) [ISI Web of Knowledge](#).
- [7] Kostishko B.M., Nagornov Yu.S., Salomatin S.Ya., “The interface model of photoluminescence of carbonized porous silicon”, *Physics of low-dimensional structures*, **3** (2004), 51–57 [ISI Web of Knowledge](#).
- [8] Костишко Б.М., Нагорнов Ю.С., Атажанов Ш.Р., Миков С.Н., “Особенности фотолюминесценции нанокристаллитов карбида кремния кубической модификации, легированного галлием”, *Письма в ЖТФ*, **28**:17 (2002), 74–81; Kostishko B.M., Nagornov Yu.S., Atazhanov Sh.R., Mikov S.N., “The features of photoluminescence from nanograins of gallium-doped cubic silicon carbide”, *Technical Physics Letters*, **28**:9 (2002), 743–745 [crossref](#) [ISI Web of Knowledge](#).
- [9] Kostishko B.M., Nagornov Yu.S., “The kinetics of destruction of molecular complexes adsorbed on a porous silicon surface by electron-beam irradiation at different densities”, *Vacuum*, **68**:3 (2002), 245–249 [crossref](#) [ISI Web of Knowledge](#).
- [10] Kostishko B.M., Nagornov Yu.S., “Water after-etching of n-type porous silicon in an electric field”, *Technical Physics*, **46**:7 (2001), 847–852 [crossref](#) [ISI Web of Knowledge](#).
- [11] Kostishko B.M., Nagornov Yu.S., “The mechanism of photoluminescence quenching in porous silicon by electron irradiation of various intensity”, *Technical Physics Letters*, **27**:10 (2001), 827–829 [crossref](#) [ISI Web of Knowledge](#).
- [12] Kostishko B.M., Nagornov Yu.S., “Water after-etching of porous silicon in the presence of electric field”, *Physics of low-dimensional structures*, **9** (2001), 87–94 [ISI Web of Knowledge](#).
- [13] Kostishko B.M., Puzov I.P., Nagornov Yu.S., “Stabilization of luminous properties of porous silicon by vacuum annealing at high temperatures”, *Technical Physics Letters*, **26**:1 (2000), 26–28 [crossref](#) [ads*](#) [ISI Web of Knowledge](#).
- [14] Kostishko B.M., Atazhanov Sh.R., Shibaev P.V., Nagornov Yu.S., “Role of resonant charge-exchange in photoluminescence of B-doped carbonized porous silicon”, *Physics of low-dimensional structures*, **7** (2000), 47–52 [ISI Web of Knowledge](#).
- [15] Kostishko B.M., Atazhanov Sh.R., Puzov I.P., Solomatin S.Ya., Nagornov Yu.S., “Heterogeneous effect in carbonized porous silicon”, *Technical Physics Letters*, **26**:3 (2000), 199–201 [crossref](#) [ISI Web of Knowledge](#).
- [16] Kostishko B.M., Puzov I.P., Nagornov Yu.S., “Stabilization of Light-Emitting Properties of Porous Silicon Thermal Vacuum Annealing”, *Technical Physics Letters*, **26**:1 (2000), 50–55.

- [17] Kostishko B.M., Guseva M.B., Khvostov V.V., Babaev V.G., Nagornov Yu.S., “Activation energy of the electron-beam-stimulated quenching of photoluminescence in porous silicon”, *Physics of low-dimensional structures*, **7** (1999), 9–14 [ISI Web of Knowledge](#).
- [18] Kostishko B.M., Atazhanov Sh.R., Puzov I.P., Salomatin S.Ya., Nagornov Yu.S., “Significance of heterojunctions in photoluminescence of carbonized porous silicon”, *Physics of low-dimensional structures*, **12** (1999), 1–6 [ISI Web of Knowledge](#).
- [19] Kostishko B.M., Nagornov Yu.S., Guseva M.B., Khvostov V.V., Babaev V.G., “Activation energy of the electron-beam-stimulated quenching of photoluminescence in porous silicon”, *Physics of Low-Dimensional Structures*, **1999:7-8** (1999), 9–14.